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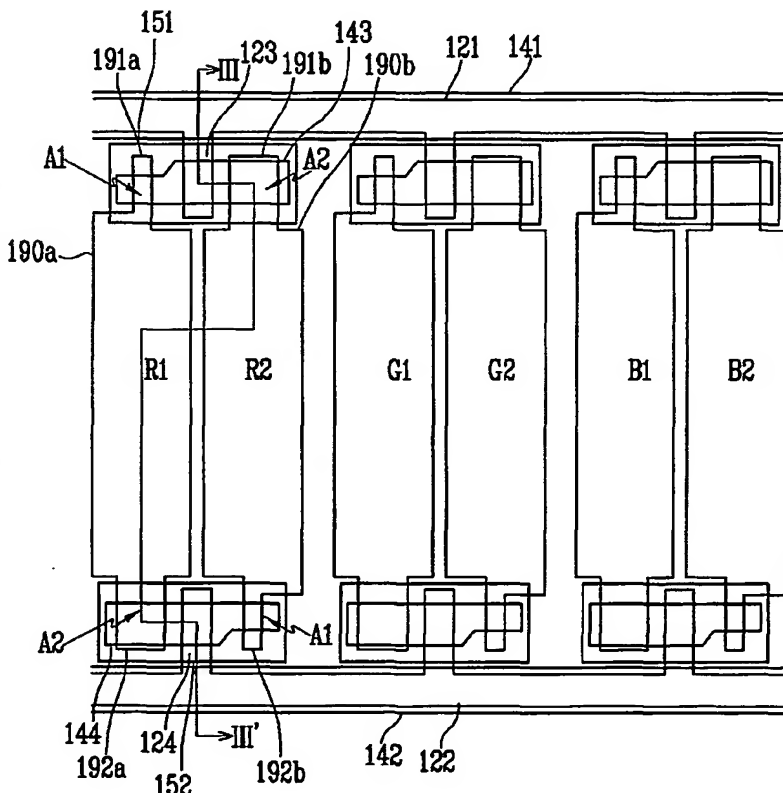
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(54) Title: **THIN FILM DIODE PANEL FOR TRANS-REFLECTECTIVE LIQUID CRYSTAL DISPLAY**



(57) Abstract: A thin film diode panel has a insulating substrate, a first and second gate lines (121, 122) formed on the insulating substrate, a reflection electrode (190a) and a transmission electrode (190b) formed on the insulating substrate, A first MIM diode (D1) is formed on the insulating substrate and connected to the first gate line (121) and the reflection electrode (190a). A second MIM diode (D2) is formed on the insulating substrate and connected to the second gate line (122) and the reflection electrode (190a). A third MIM diode (D1) is formed on the insulating substrate and connecting the first gate line (121) and the transmission electrode (190b). A fourth MIM diode (D21) is formed on the insulating substrate and connecting the second gate line (122) and the transmission electrode (190b). At least one of the first to fourth MIM diodes has a substantially different current-voltage (I-V) characteristic from the others.



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